

### **SPECIFICATION AMENDMENTS:**

Please replace the paragraph on page 1, lines 15 through 21, with the following amended paragraph:

--In the semiconductor apparatus that employs the BGA structure, for example, very small solder balls having diameters of about 0.5 to 0.7 mm are arranged in an array to be apart from one ~~another~~ another at predetermined intervals, which function as external electrodes. Thus, many external electrodes are densely disposed ~~highly densely~~ on one surface of the semiconductor apparatus, consequently providing a package which enables transfer of many signals between the outside and the semiconductor devices.--

Please replace the paragraph on page 6, lines 7 through 9, with the following amended paragraph:

--Each of the plurality of openings 106 is can be formed in the mask 104 so that an area 106b of the opening 106 in the lower surface ~~can be~~ is larger than an area 106a thereof in the upper surface.--

Please replace the paragraph on page 7, lines 2 through 7, with the following amended paragraph:

--After the removal of the surplus solder balls and the insertion of the solder balls into the openings 106, the semiconductor apparatus 101 is heated by, for ~~example~~ example, reflowing or the like of to about 220 to 260°C while the mask

104 is kept fixed on the surface. Thus, the solder balls on the fluxes 103 are melted to be deposited on the electrode pads 102. Accordingly, a ball electrode of the semiconductor apparatus 101 is formed.--